30V COMPLEMENTARY ENHANCEMENT MODE MOSFET

Product Summary

Device	BV_{DSS}	$R_{DS(ON)}$ Max	Package	I_D Max T_A = +25°C
N-Channel	30V	20mΩ @ V_{GS} = 10V	SO-8	8.5A
		32mΩ @ V_{GS} = 4.5V		7.0A
P-Channel	-30V	45mΩ @ V_{GS} = -10V		-5.5A
		85mΩ @ V_{GS} = -4.5V		-4.1A

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMC3025LSDQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**
  https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- DC motor control
- DC-AC inverters

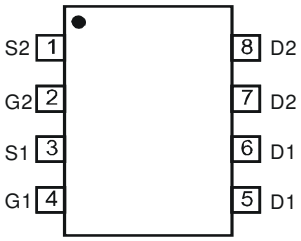
Mechanical Data

- Package: SO-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish – Matte Tin Annealed Over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.074 grams (Approximate)

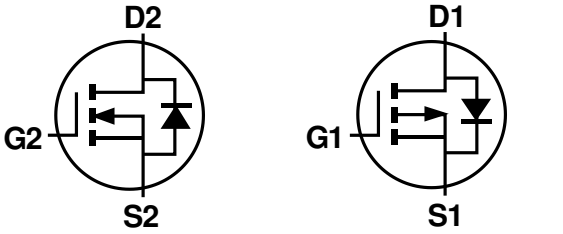
SO-8



Top View



Pin Configuration



Q2 N-CHANNEL MOSFET Q1 P-CHANNEL MOSFET

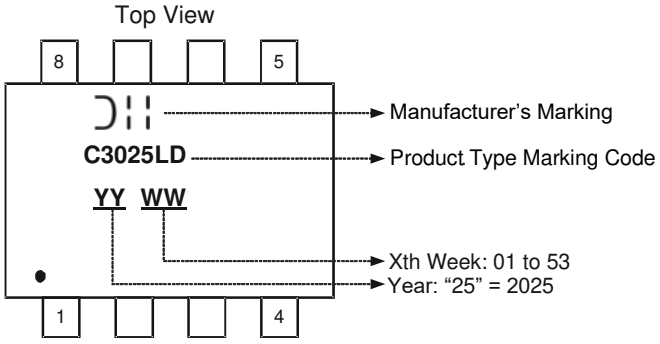
Equivalent Circuit

Ordering Information (Note 5)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMC3025LSDQ-13	SO-8	2,500	Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



© 2025 Copyright Diodes Incorporated. All Rights Reserved.

Maximum Ratings N-CHANNEL – Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 5) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	6.5 5.1	A
	t < 10s	T_A = +25°C T_A = +70°C	I_D	8.5 6.8	A
Continuous Drain Current (Note 5) V_{GS} = 4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	5.3 4.1	A
	t < 10s	T_A = +25°C T_A = +70°C	I_D	7.0 5.5	A
Maximum Continuous Body Diode Forward Current (Note 5)			I_S	2	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	60	A
Pulsed Body Diode Current (10µs Pulse, Duty Cycle = 1%)			I_{SM}	60	A
Avalanche Current (Note 6) L = 0.1mH			I_{AS}	14	A
Avalanche Energy (Note 6) L = 0.1mH			E_{AS}	10	mJ

Maximum Ratings P-CHANNEL – Q1 (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 5) V_{GS} = -10V	Steady State	T_A = +25°C T_A = +70°C	I_D	-4.2 -3.2	A
	t < 10s	T_A = +25°C T_A = +70°C	I_D	-5.5 -4.3	A
Continuous Drain Current (Note 5) V_{GS} = -4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	-3.5 -2.3	A
	t < 10s	T_A = +25°C T_A = +70°C	I_D	-4.1 -3.2	A
Maximum Continuous Body Diode Forward Current (Note 5)			I_S	-2	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	-30	A
Pulsed Body Diode Current (10µs Pulse, Duty Cycle = 1%)			I_{SM}	-30	A
Avalanche Current (Note 6) L = 0.1mH			I_{AS}	-14	A
Avalanche Energy (Note 6) L = 0.1mH			E_{AS}	10	mJ

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
6. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

© 2025 Copyright Diodes Incorporated. All Rights Reserved.

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 7)	T_A = +25°C	P_D	1.2	W
	T_A = +70°C		0.77	
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	$R_{\theta JA}$	104	°C/W
	t < 10s		62	
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	1.5	W
	T_A = +70°C		0.95	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	83	°C/W
	t < 10s		49	
Thermal Resistance, Junction to Case (Note 5)		$R_{\theta JC}$	15	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics N-CHANNEL – Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0, I_D = 250μA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	V_{DS} = 30V, V_{GS} = 0
Gate-Source Leakage	I_{GSS}	—	—	±1	μA	V_{GS} = ±20V, V_{DS} = 0
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.0	—	2.0	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	15	20	mΩ	V_{GS} = 10V, I_D = 7.4A
		—	23	32		V_{GS} = 4.5V, I_D = 6A
Forward Transfer Admittance	$\|Y_{FS}\|$	—	8	—	S	V_{DS} = 5V, I_D = 10A
Diode Forward Voltage	V_{SD}	—	0.70	1.2	V	V_{GS} = 0, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	501	—	pF	V_{DS} = 15V, V_{GS} = 0, f = 1.0MHz
Output Capacitance	C_{oss}	—	72	—		
Reverse Transfer Capacitance	C_{rss}	—	57	—		
Gate Resistance	R_g	—	1.84	—	Ω	V_{DS} = 0, V_{GS} = 0, f = 1.0MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	4.6	—	nC	V_{DS} = 15V, I_D = 10A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	9.8	—		
Gate-Source Charge	Q_{gs}	—	1.6	—		
Gate-Drain Charge	Q_{gd}	—	2.0	—		
Turn-On Delay Time	$t_{D(ON)}$	—	3.9	—	ns	V_{DD} = 15V, V_{GS} = 10V, R_g = 6Ω, I_D = 1A
Turn-On Rise Time	t_R	—	4.2	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	16.6	—		
Turn-Off Fall Time	t_F	—	5.8	—		
Reverse-Recovery Time	t_{RR}	—	5.5	—	ns	I_F = 12A, di/dt = 500A/μs
Reverse-Recovery Charge	Q_{RR}	—	2.6	—	nC	

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
6. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
7. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

© 2025 Copyright Diodes Incorporated. All Rights Reserved.

Electrical Characteristics P-CHANNEL – Q1 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	V_{GS} = 0, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	µA	V_{DS} = -30V, V_{GS} = 0
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	-1.0	—	-2.0	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	38	45	mΩ	V_{GS} = -10V, I_D = -5.2A
		—	65	85		V_{GS} = -4.5V, I_D = -4A
Forward Transfer Admittance	$\|Y_{FS}\|$	—	5	—	S	V_{DS} = -5V, I_D = -5.2A
Diode Forward Voltage	V_{SD}	—	-0.7	-1.2	V	V_{GS} = 0, I_S = -1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	590	—	pF	V_{DS} = -25V, V_{GS} = 0, f = 1.0MHz
Output Capacitance	C_{oss}	—	69	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	53	—	pF	
Gate resistance	R_g	—	11	—	Ω	V_{DS} = 0, V_{GS} = 0, f = 1.0MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	5.1	—	nC	V_{DS} = -15V, I_D = -6A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	10.5	—	nC	
Gate-Source Charge	Q_{gs}	—	1.8	—	nC	
Gate-Drain Charge	Q_{gd}	—	1.9	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	6.8	—	ns	V_{DD} = -15V, V_{GS} = -10V, R_g = 6Ω, I_D = -1A
Turn-On Rise Time	t_R	—	4.9	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	28.4	—	ns	
Turn-Off Fall Time	t_F	—	12.4	—	ns	
Reverse-Recovery Time	t_{RR}	—	14	—	ns	I_F = 12A, di/dt = 500A/µs
Reverse-Recovery Charge	Q_{RR}	—	11	—	nC	

Notes: 8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

© 2025 Copyright Diodes Incorporated. All Rights Reserved.

N-CHANNEL

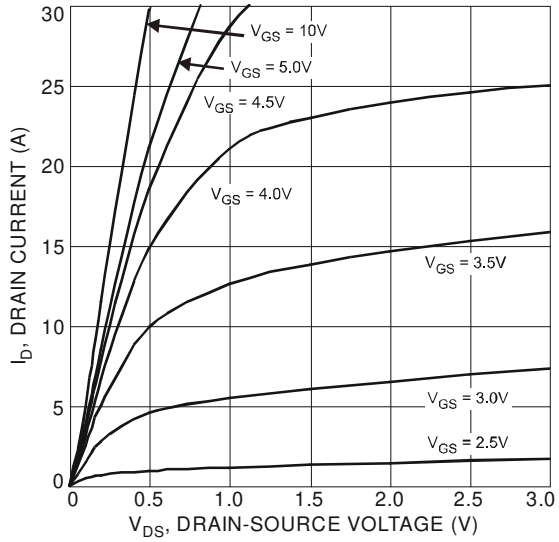


Figure 1. Typical Output Characteristic

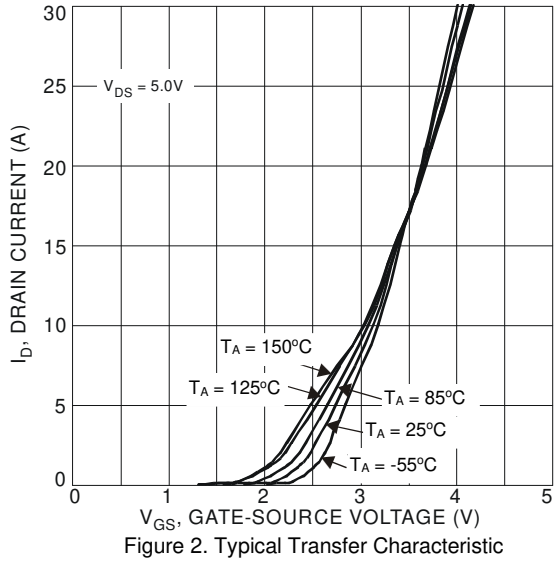


Figure 2. Typical Transfer Characteristic

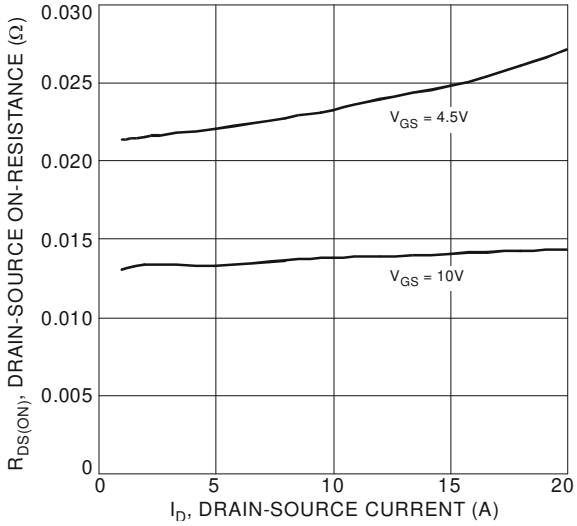


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

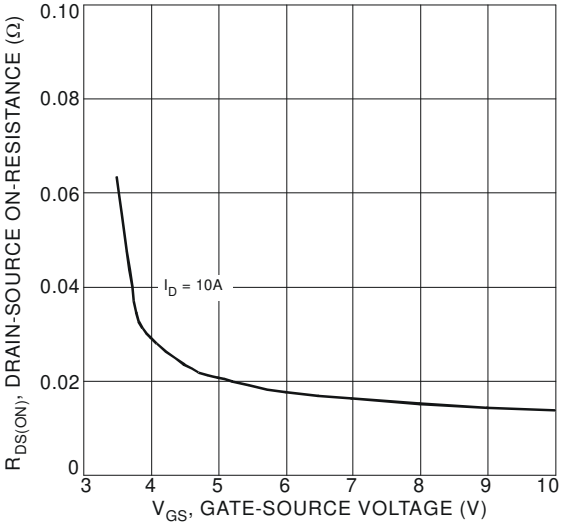


Figure 4. Typical On-Resistance vs. Drain Current and Gate Voltage

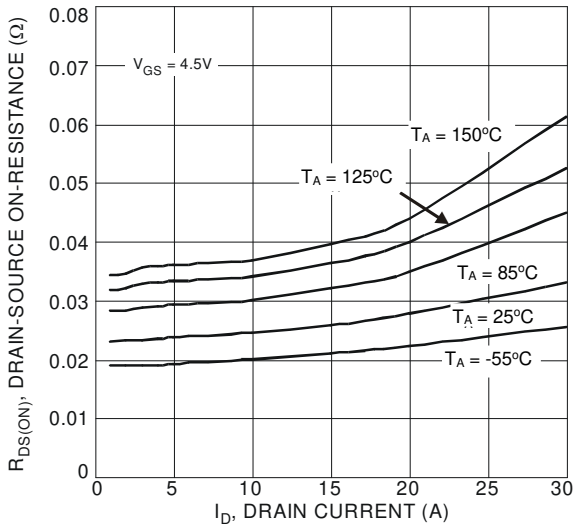


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

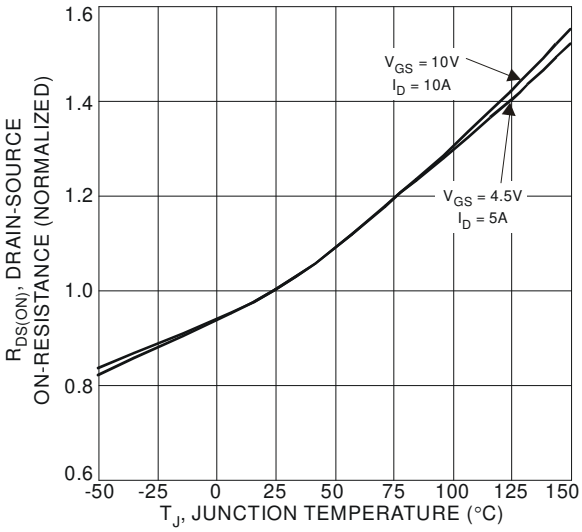


Figure 6. On-Resistance Variation with Temperature

© 2025 Copyright Diodes Incorporated. All Rights Reserved.

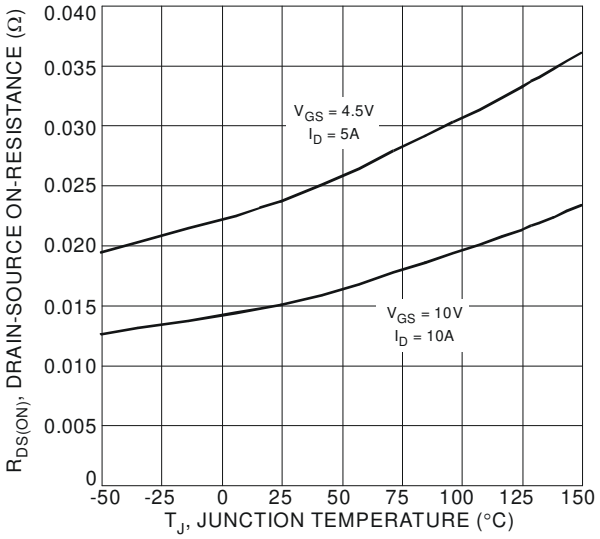


Figure 7. On-Resistance Variation with Temperature

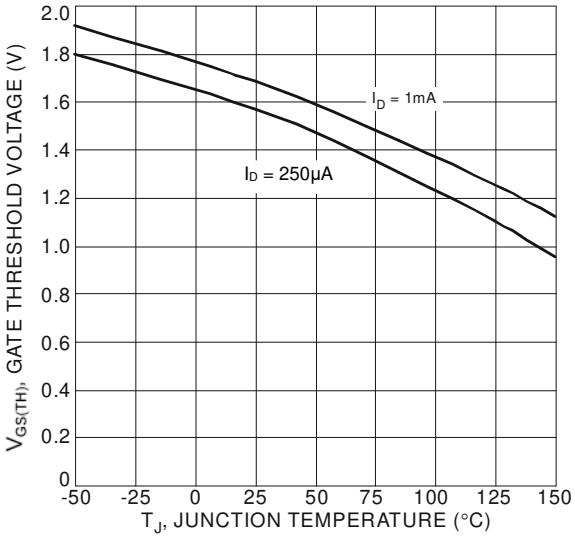


Figure 8. Gate Threshold Variation vs. Ambient Temperature

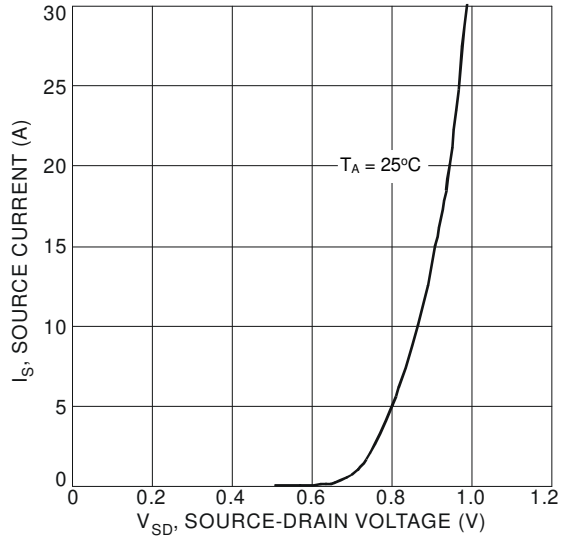


Figure 9. Diode Forward Voltage vs. Current

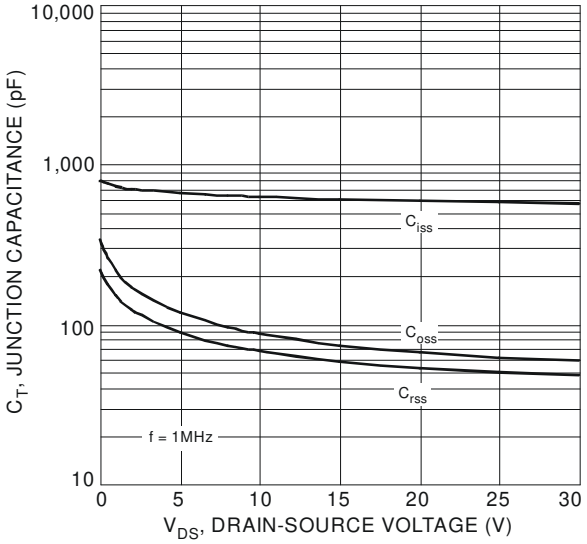


Figure 10. Typical Junction Capacitance

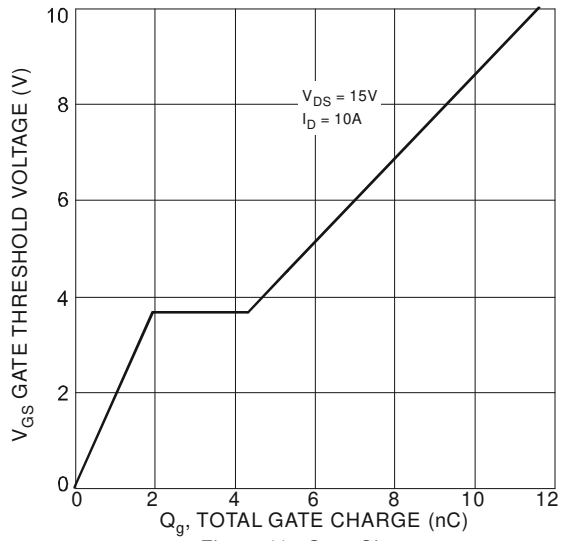


Figure 11. Gate Charge

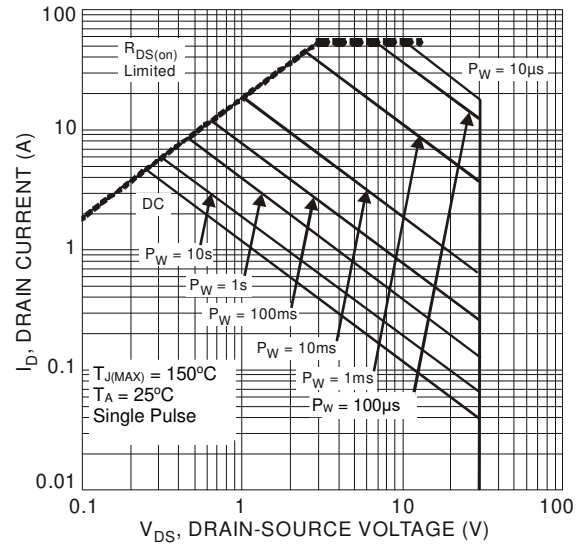


Figure 12. SOA, Safe Operation Area

© 2025 Copyright Diodes Incorporated. All Rights Reserved.

P-CHANNEL

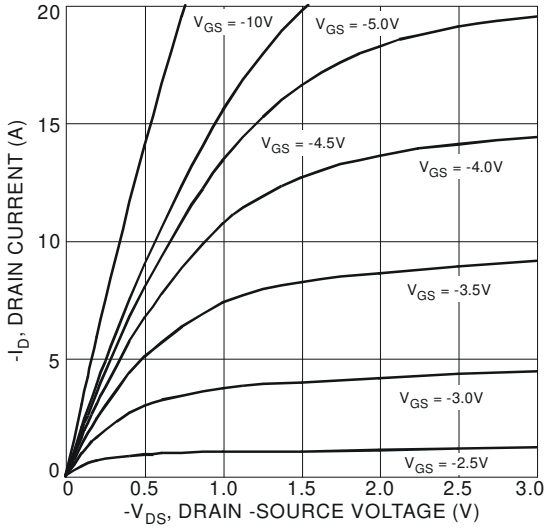


Figure 13. Typical Output Characteristics

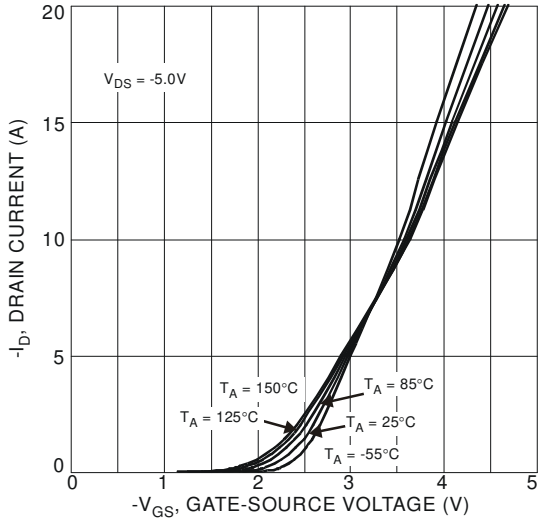


Figure 14. Typical Transfer Characteristics

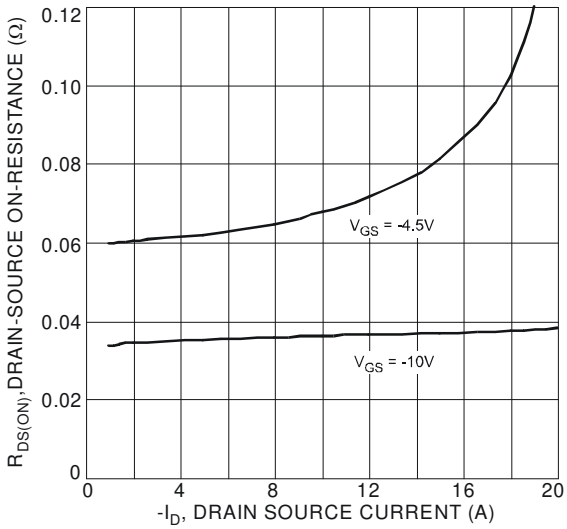


Figure 15. Typical On-Resistance vs. Drain Current and Gate Voltage

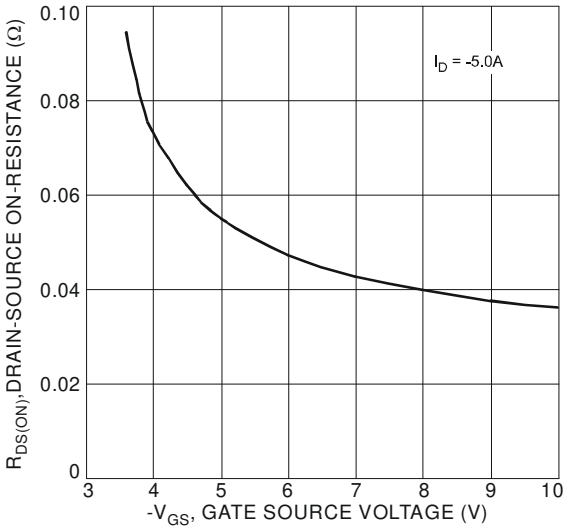


Figure 16. Typical On-Resistance vs. Drain Current and Gate Voltage

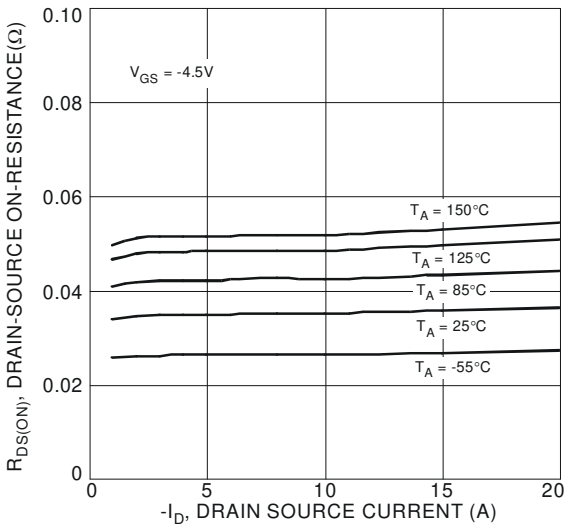


Figure 17. Typical On-Resistance vs. Drain Current and Temperature

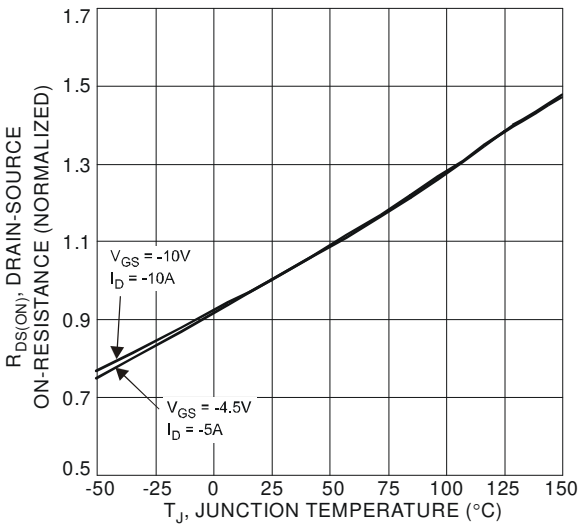


Figure 18. On-Resistance Variation with Temperature

© 2025 Copyright Diodes Incorporated. All Rights Reserved.

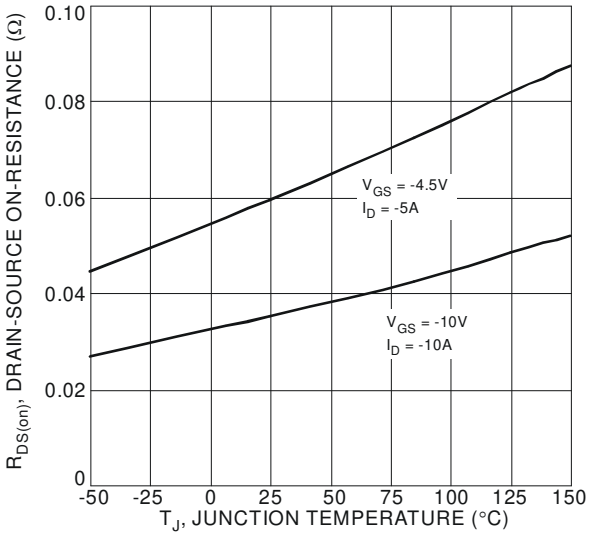


Figure 19. On-Resistance Variation with Temperature

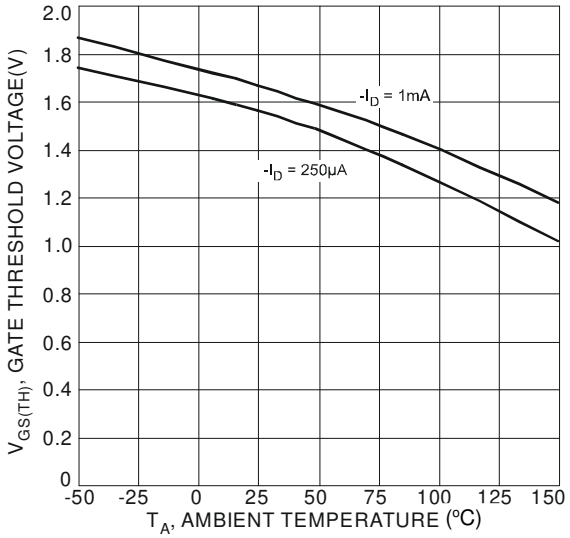


Figure 20. Gate Threshold Variation vs. Ambient Temperature

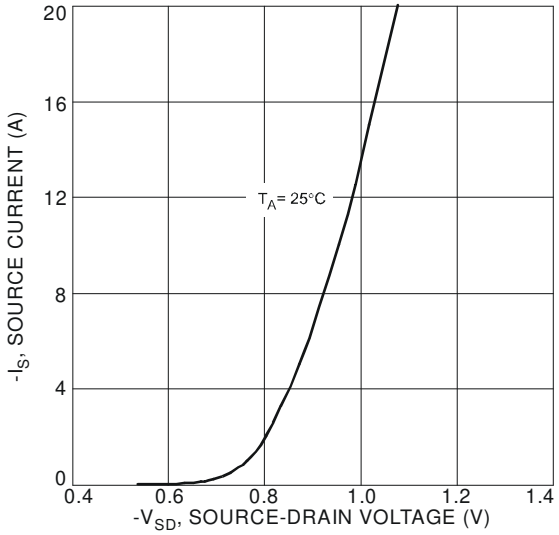


Figure 21. Diode Forward Voltage vs. Current

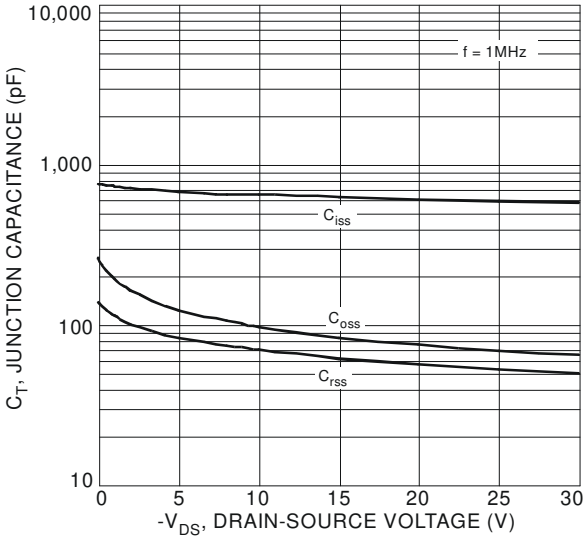


Figure 22. Typical Junction Capacitance

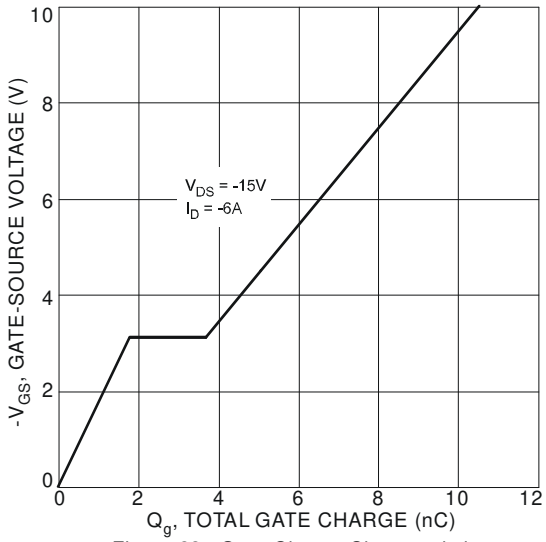


Figure 23. Gate-Charge Characteristics

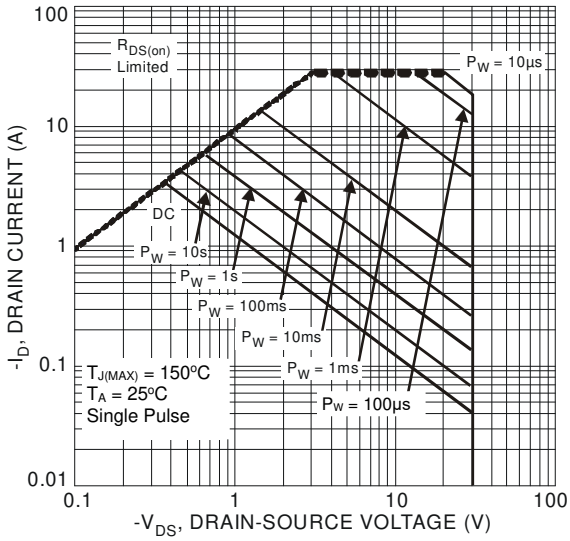


Figure 24. SOA, Safe Operation Area

© 2025 Copyright Diodes Incorporated. All Rights Reserved.

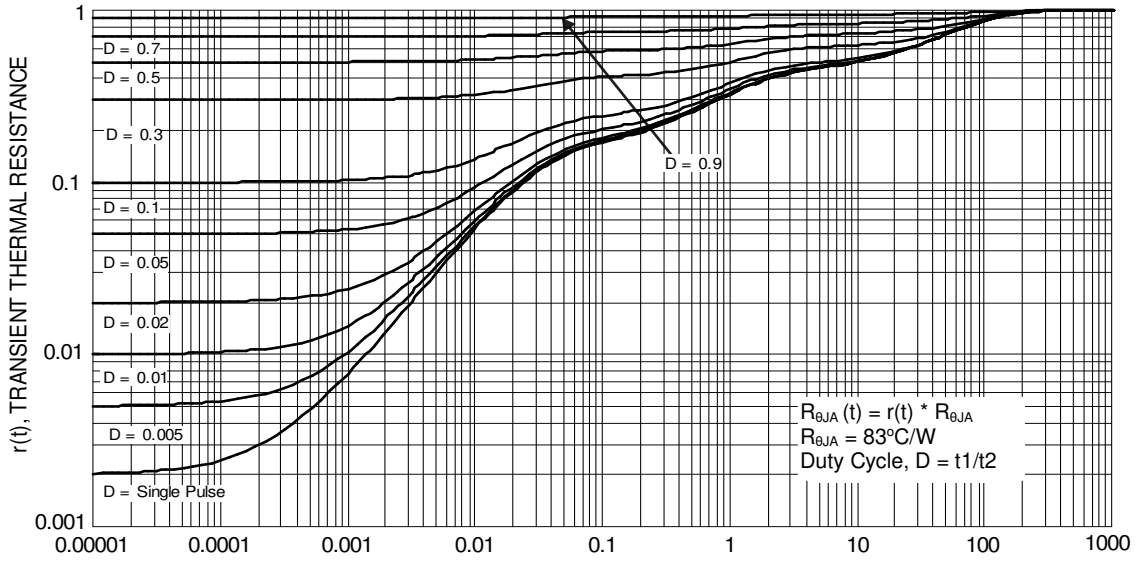


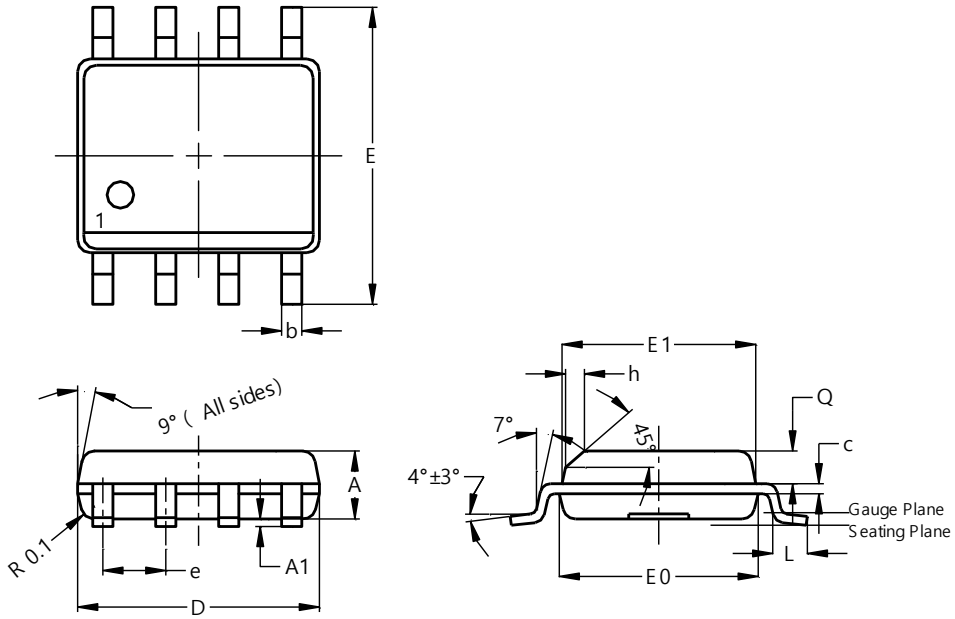
Figure 25. Transient Thermal Resistance

© 2025 Copyright Diodes Incorporated. All Rights Reserved.

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8

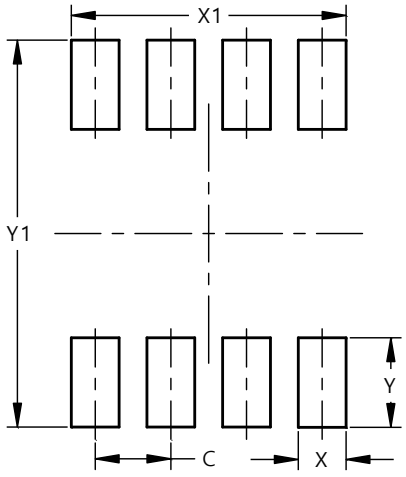


SO-8			
Dim	**Min**	**Max**	**Typ**
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	-	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

© 2025 Copyright Diodes Incorporated. All Rights Reserved.

IMPORTANT NOTICE

1. DIODES INCORPORATED (Diodes) AND ITS SUBSIDIARIES MAKE NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO ANY INFORMATION CONTAINED IN THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

2. The Information contained herein is for informational purpose only and is provided only to illustrate the operation of Diodes' products described herein and application examples. Diodes does not assume any liability arising out of the application or use of this document or any product described herein. This document is intended for skilled and technically trained engineering customers and users who design with Diodes' products. Diodes' products may be used to facilitate safety-related applications; however, in all instances customers and users are responsible for (a) selecting the appropriate Diodes products for their applications, (b) evaluating the suitability of Diodes' products for their intended applications, (c) ensuring their applications, which incorporate Diodes' products, comply the applicable legal and regulatory requirements as well as safety and functional-safety related standards, and (d) ensuring they design with appropriate safeguards (including testing, validation, quality control techniques, redundancy, malfunction prevention, and appropriate treatment for aging degradation) to minimize the risks associated with their applications.

3. Diodes assumes no liability for any application-related information, support, assistance or feedback that may be provided by Diodes from time to time. Any customer or user of this document or products described herein will assume all risks and liabilities associated with such use, and will hold Diodes and all companies whose products are represented herein or on Diodes' websites, harmless against all damages and liabilities.

4. Products described herein may be covered by one or more United States, international or foreign patents and pending patent applications. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks and trademark applications. Diodes does not convey any license under any of its intellectual property rights or the rights of any third parties (including third parties whose products and services may be described in this document or on Diodes' website) under this document.

5. Diodes' products are provided subject to Diodes' Standard Terms and Conditions of Sale (https://www.diodes.com/about/company/terms-and-conditions/terms-and-conditions-of-sales/) or other applicable terms. This document does not alter or expand the applicable warranties provided by Diodes. Diodes does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.

6. Diodes' products and technology may not be used for or incorporated into any products or systems whose manufacture, use or sale is prohibited under any applicable laws and regulations. Should customers or users use Diodes' products in contravention of any applicable laws or regulations, or for any unintended or unauthorized application, customers and users will (a) be solely responsible for any damages, losses or penalties arising in connection therewith or as a result thereof, and (b) indemnify and hold Diodes and its representatives and agents harmless against any and all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim relating to any noncompliance with the applicable laws and regulations, as well as any unintended or unauthorized application.

7. While efforts have been made to ensure the information contained in this document is accurate, complete and current, it may contain technical inaccuracies, omissions and typographical errors. Diodes does not warrant that information contained in this document is error-free and Diodes is under no obligation to update or otherwise correct this information. Notwithstanding the foregoing, Diodes reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes.

8. Any unauthorized copying, modification, distribution, transmission, display or other use of this document (or any portion hereof) is prohibited. Diodes assumes no responsibility for any losses incurred by the customers or users or any third parties arising from any such unauthorized use.

9. This Notice may be periodically updated with the most recent version available at https://www.diodes.com/about/company/terms-and-conditions/important-notice

The Diodes logo is a registered trademark of Diodes Incorporated in the United States and other countries.
All other trademarks are the property of their respective owners.
© 2025 Diodes Incorporated. All Rights Reserved.

www.diodes.com

© 2025 Copyright Diodes Incorporated. All Rights Reserved.